## SUM40010EL

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Vishay Siliconix

ROHS COMPLIANT

HALOGEN

FREE

# N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A) <sup>d</sup>	Q <sub>g</sub> (TYP.)			
40	0.0016 at V <sub>GS</sub> = 10 V	120	150			
	0.0019 at V <sub>GS</sub> = 4.5 V	120	130			



**Ordering Information:** 

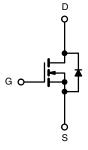
SUM40010EL-GE3 (lead (Pb)-free and halogen-free)

#### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- Maximum 175 °C junction temperature
- Q<sub>gd</sub>/Q<sub>gs</sub> ratio < 0.5
- Operable with logic-level gate drive
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- Power supply
  Secondary synchronous rectification
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \text{ °C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V <sub>DS</sub>	40	v			
Gate-Source Voltage	V <sub>GS</sub>	± 20	v			
Continuous Drain Current (T. 150 °C)	T <sub>C</sub> = 25 °C		120 <sup>d</sup>	А		
Continuous Drain Current ( $T_J = 150 \text{ °C}$ )	T <sub>C</sub> = 70 °C	– I <sub>D</sub>	120 <sup>d</sup>			
Pulsed Drain Current (t = 100 μs)	I <sub>DM</sub>	300	A			
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	80			
Single Avalanche Energy <sup>a</sup>		E <sub>AS</sub>	320	mJ		
Marian Barran Diasia atian 8	T <sub>C</sub> = 25 °C	- PD	375 <sup>b</sup>	w		
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	FD	125 <sup>b</sup>	vv		
Operating Junction and Storage Temperature F	lange	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.4	0/10		

#### Notes

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

d. Package limited.

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**SUM40010EL** 

<b>SPECIFICATIONS</b> ( $T_J = 25 \text{ °C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$	40	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1.2	-	2.5	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 250	nA	
		$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	^	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	150	μA	
		$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	5	mA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	120	-	-	А	
Drain-Source On-State Resistance a	P	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	-	0.00127	0.00160	Ω	
Drain-Source On-State Resistance "	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	0.00152	0.00190		
Forward Transconductance a	<b>g</b> fs	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	-	174	-	S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		-	11 155	-	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 30 V, f = 1 MHz	-	7410	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	880	-		
Total Gate Charge <sup>c</sup>	Qg		-	150	230		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS}$ = 20 V, $V_{GS}$ = 10 V, $I_{D}$ = 20 A	-	32	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	11	-		
Gate Resistance	Rg	f = 1 MHz	0.32	1.6	3.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	16	32	ns	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 5 $\Omega$	-	20	40		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A},  V_{GEN} = 10  \text{V},  \text{R}_\text{g} = 1  \Omega$	-	65	100		
Fall Time <sup>c</sup>	t <sub>f</sub>		-	17	35		
Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (T <sub>C</sub> = 25 °C)							
Pulsed Current (t = 100 µs)	I <sub>SM</sub>		-	-	300	А	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_F = 10 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>		-	135	203	ns	
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>	I <sub>F</sub> = 41 A, di/dt = 100 A/µs	-	5	10	А	
Reverse Recovery Charge	Q <sub>rr</sub>		-	0.340	0.510	μC	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

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c. Independent of operating temperature.

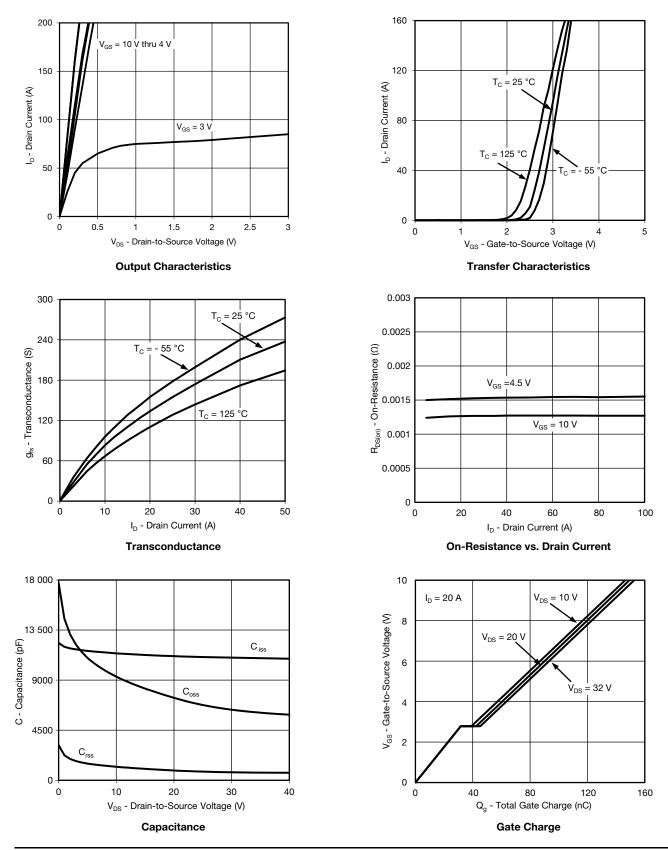
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



S15-2184-Rev. A, 14-Sep-15

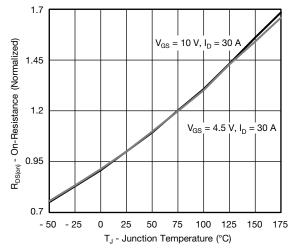
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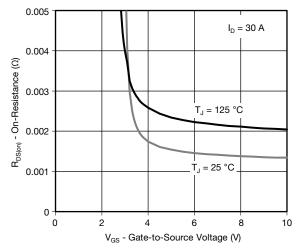




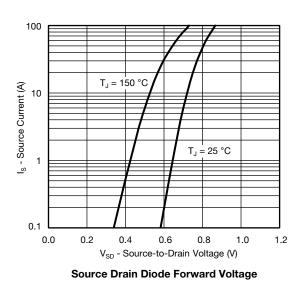
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



**On-Resistance vs. Junction Temperature** 

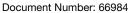


**On-Resistance vs. Gate-to-Source Voltage** 



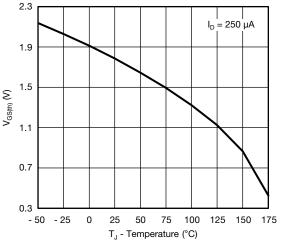
S15-2184-Rev. A, 14-Sep-15

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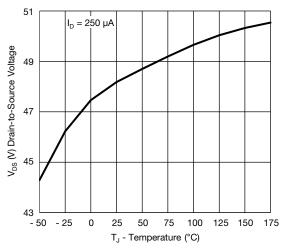


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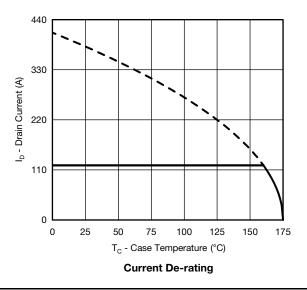
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**Threshold Voltage** 



Drain Source Breakdown vs. Junction Temperature

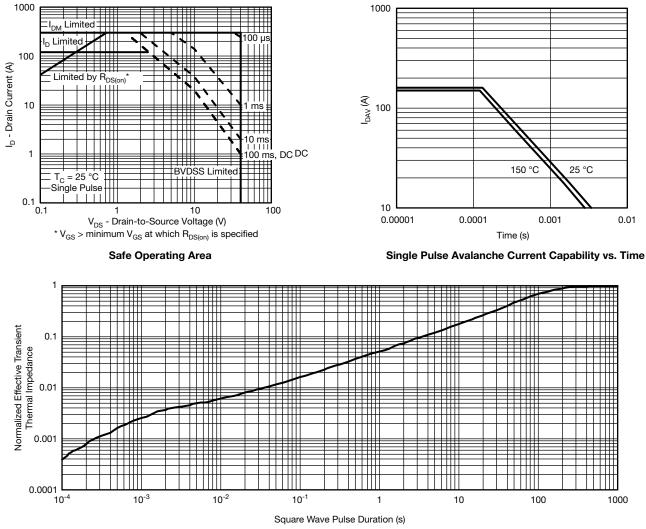


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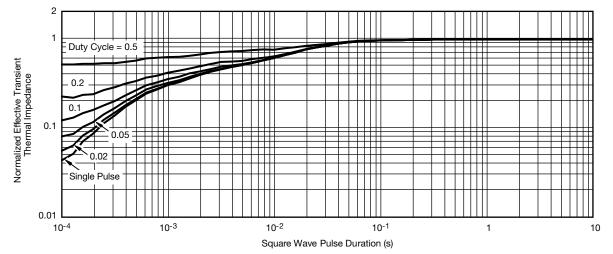
### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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TO-263 (D<sup>2</sup>PAK): 3-LEAD

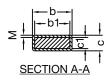








DETAIL A (ROTATED 90°)



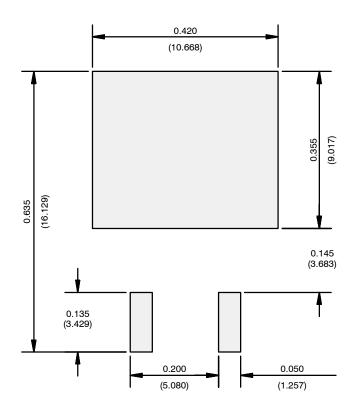
		INC	HES	MILLIMETERS			
DIM.		MIN.	MAX.	MIN.	MAX.		
	А	0.160	0.190	4.064	4.826		
	b	0.020	0.039	0.508	0.990		
	b1	0.020	0.035	0.508	0.889		
	b2	0.045	0.055	1.143	1.397		
с*	Thin lead	0.013	0.018	0.330	0.457		
C	Thick lead	0.023	0.028	0.584	0.711		
c1	Thin lead	0.013	0.017	0.330	0.431		
CI	Thick lead	0.023	0.027	0.584	0.685		
	c2	0.045	0.055	1.143	1.397		
	D	0.340	0.380	8.636	9.652		
	D1	0.220	0.240	5.588	6.096		
	D2	0.038	0.042	0.965	1.067		
D3		0.045	0.055	1.143	1.397		
	D4	0.044	0.052	1.118	1.321		
	E	0.380	0.410	9.652	10.414		
	E1	0.245	-	6.223	-		
	E2	0.355	0.375	9.017	9.525		
	E3	0.072	0.078	1.829	1.981		
	е	0.100	0.100 BSC		BSC		
	К	0.045	0.055	1.143	1.397		
	L	0.575	0.625	14.605	15.875		
	L1	0.090	0.110	2.286	2.794		
	L2	0.040	0.055	1.016	1.397		
	L3	0.050	0.070	1.270	1.778		
	L4	0.010 BSC 0.254 BS		BSC			
	М	-	0.002	- 0.050			
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843							

#### Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB.
  - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.
- 6. This feature is for thick lead.



### **RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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